

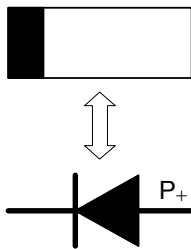
## SMD Schottky Barrier Diode

### ■ Features

$$I_O = 200\text{mA}$$

$$V_R = 30\text{V}$$

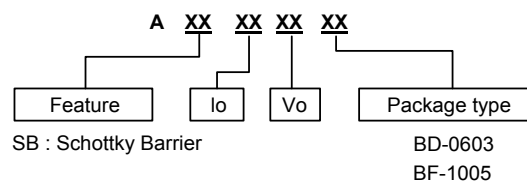
- Designed for mounting on small surface.
- Extremely thin package.
- Low drop-down voltage.
- Majority carrier conduction
- Lead-free device



### ■ Mechanical Data

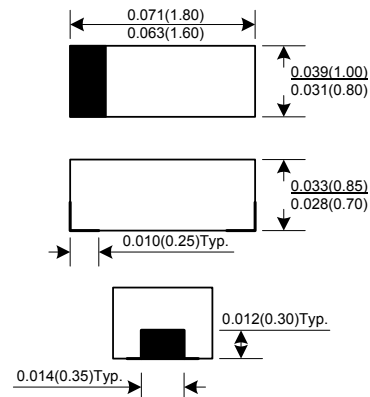
- Case :0603(1608) 1005(2512) standard package, molded plastic.
- Terminals : Gold plated, solderable per MIL-STD-750, method 2026.
- Polarity : Indicated by cathode band.
- Mounting position : Any.
- Weight : BD:0.003gram (approximately)  
BF:0.006gram (approximately)

### ■ Ordering information



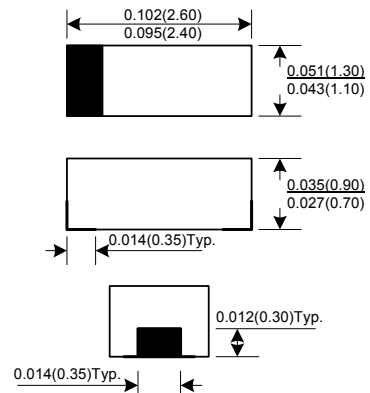
### ■ General Description

0603(1608)



Dimensions in inches and (millimeter)

1005(2512)



Dimensions in inches and (millimeter)

**SMD Schottky Barrier Diode**

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**■ Maximum Rating (at  $T_A=25^\circ\text{C}$  unless otherwise noted)**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit	
$V_{RRM}$	Repetitive peak reverse voltage		-	-	35	V	
$V_R$	Reverse voltage		-	-	30	V	
$I_O$	Average forward current		-	-	200	mA	
$I_{FSM}$	Forward current, surge peak	0603	8.3ms single half sine-wave superimposed on rate load (JEDEC method)	-	2000	-	mA
		1005		-	3000	-	
$P_D$	Power Dissipation	0603	-	-	150	mW	
		1005	-	-	250		
$T_{STG}$	Storage temperature		-40	-	+125	$^\circ\text{C}$	
$T_j$	Junction temperature		-40	-	+125	$^\circ\text{C}$	

**■ Electrical Characteristics (at  $T_A=25^\circ\text{C}$  unless otherwise noted)**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$V_F$	Forward voltage	$I_F=200\text{mA DC}$	-	-	0.50	V
$I_R$	Reverse current	$V_R=30\text{V}$	-	-	30	$\mu\text{A}$
$C_T$	Capacitance between terminals	$F=1\text{MHz}$ , and 10 VDC reverse voltage	-	9	-	pF

Rating And Characteristic Curves

Fig. 1 - Forward characteristics

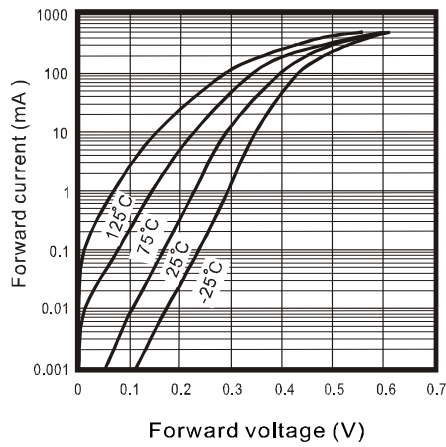


Fig. 2 - Reverse characteristics

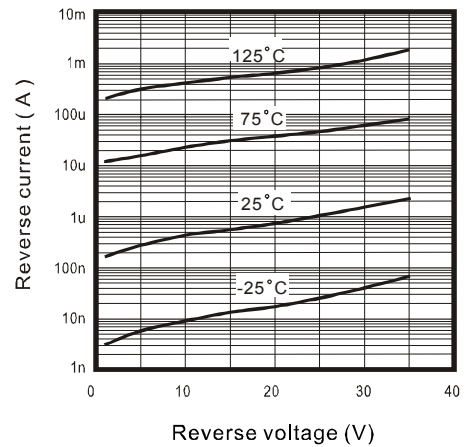


Fig. 3 - Capacitance between terminals characteristics

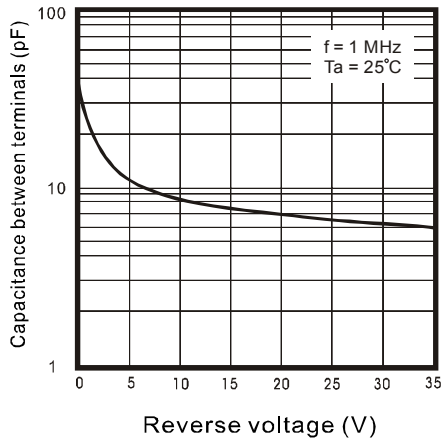
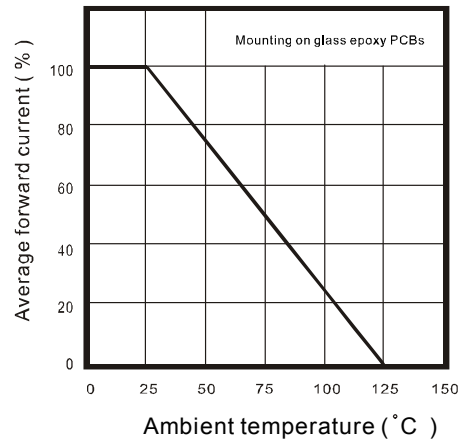


Fig. 4 - Current derating curve



Marking Information

